

A Laterally Diffused Metal Oxide  
Semiconductor Device and a Method of Manufacture Therefor

Abstract of the Disclosure

A laterally diffused metal oxide semiconductor (LDMOS) device  
5 and a method of manufacture therefor. The method of manufacturing  
the LDMOS device includes forming an amorphous region in a  
semiconductor substrate between isolation structures and adjacent  
a gate structure, by implanting an amorphizing element, such as  
silicon or germanium, in the semiconductor substrate. The method  
10 further includes diffusing a first source/drain dopant laterally in  
the amorphous region to form a first portion of a channel.